

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	22	((BERNARD) near2 (BECHEVET)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:09
S1	1	((PETER) near2 (HARING-BOLIVAR)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:09
S3	9	((VERONIQUE) near2 (SOUSA)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:10
S6	1	((FLORIAN) near2 (MERGET)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:11
S5	17	((HEINRICH) near2 (KUFZ)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:11
S4	1	((DAE-HWANG) near2 (KIM)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:11
S8	5	US-6854033-\$.DID. OR US-7214632-\$.DID. OR US-7227171-\$.DID. OR US-7358521-\$.DID. OR US-20080002457-\$.DID.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:14
S7	9	US-3448302-\$.DID. OR US-4420766-\$.DID. OR US-4599705-\$.DID. OR US-4795657-\$.DID. OR US-5049971-\$.DID. OR US-6087689-\$.DID. OR US-6287887-\$.DID. OR US-6473332-\$.DID.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:14
S9	2	US-5933365-\$.DID. OR US-6525953-\$.DID.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:19
S10	44372	PCM or (phase adj change adj memory) or PRAM or PCRAM or (phase adj chang\$5 adj RAM) or (programmable adj conductor adj (RAM or memory)) or (programmable adj resistance adj2 element) or C-RAM or (Chalcogenide adj RAM) or OUM or (Ovonic adj Unified adj Memory)	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:38
S11	9	(lateral\$4 or horizon\$3) adj2 switch\$4 adj2 zone	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:39
S13	2	S10 same S12	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:40

S12	2233	switch\$4 adj2 zone	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:40
S14	30	S10 and S12	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:41
S16	3	S12 same S15	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:42
S15	19647	memory adj2 material	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:42
S17	28	S14 not S13	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:47
S18	2774	365/163,148,100.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 17:21
S19	2	S12 and S18	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 17:22
S21	3	S12 same S20	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 17:23
S20	6713	memory adj2 (layer)	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 17:23
S22	26	electrode with S12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/14 17:24
S25	26	S15 and S23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/14 19:00
S24	0	S12 and S23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/14 19:00
S23	7451	257/52-63.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/14 19:00
S26	2129	257/2-5.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/14 19:06

S27	3	S26 and S12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/14 19:07
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## EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S30	4536	(memory adj2 material). dm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:03
S29	324	(switch\$4 adj2 zone).dm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:03
S28	1	((lateral\$4 or horizon\$3) adj2 switch\$4 adj2 zone). dm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:03
S32	25	memory same S29	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:04
S31	1	S29 and S30	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:04
S33	8	electrode same S29	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:05
S34	2793	365/163,148,100.ocls.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:06
S36	5836	257/52-63.ocls.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:07
S35	2123	257/2-5.ocls.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:07
S39	5315	(PCM or (phase adj change adj memory) or PRAM or PCRAM or (phase adj chang \$5 adj RAM) or (programmable adj conductor adj (RAM or memory)) or (programmable adj resistance adj2 element) or C-RAM or (Chalcogenide adj RAM) or OUM or (Ovonic adj Unified adj Memory)).dm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:08

S38	318	S30 and (S34 or S35 or S36)	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:08
S37	3	S29 and (S34 or S35 or S36)	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:08
S40	97	S38 and S39	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:09
L10	3	8 and 9	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 08:41
L9	5315	((PCM or (phase adj change adj memory) or PPRAM or PPRAM or (phase adj change adj RAM) or (programmable adj conductor adj (RAM or memory)) or (programmable adj resistance adj2 element) or C-RAM or (Chalcogenide adj RAM) or OUM or (Ovonic adj Unified adj Memory)).clm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 08:41
L8	1052	(switch\$4 adj2 area).clm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 08:41
L11	69	electrode same L8	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 08:43
L14	1	8 and 13	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:07
L13	4536	(memory adj2 material).clm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:07
L19	4	8 and 18	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:08
L18	10333	15 or 16 or 17	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:08
L17	2793	365/163,148,100.ccls.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:08
L16	2123	257/2-5.ccls.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:08
L15	5836	257/52-63.ccls.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:08

L21	208	18 and 20	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:09
L20	801	switch\$4 same 9	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:09

**9/ 15/ 10 10:03:28 AM****C:\ Documents and Settings\ smai\ My Documents\ EAST\ Workspaces\ 10.576760.wsp**